

Title (en)

HIGH VOLTAGE COMPONENT AND METHOD FOR MAKING SAME

Title (de)

HOCHSPANNUNGSBAUELEMENT UND VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)

COMPOSANT HAUTE TENSION ET SON PROCEDE DE PRODUCTION

Publication

EP 1008182 A1 20000614 (DE)

Application

EP 98914831 A 19980228

Priority

- DE 9800597 W 19980228
- DE 19735542 A 19970816

Abstract (en)

[origin: DE19735542A1] A high voltage component has a self-supporting n-doped semiconductor wafer with two or more series-connected sub-components, at least one of which has a p-region extending from the front face to the back face of the wafer. An Independent claim is also included for production of the above component by forming uniformly spaced-apart, parallel, stripe-like p-regions in a lightly n-doped semiconductor component, the p-regions extending from the front face to the back face of the wafer and dividing the wafer into parallel lightly n-doped regions.

IPC 1-7

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IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

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